

Silicon PNP Power Transistors

2SA1306 2SA1306A 2SA1306B

DESCRIPTION

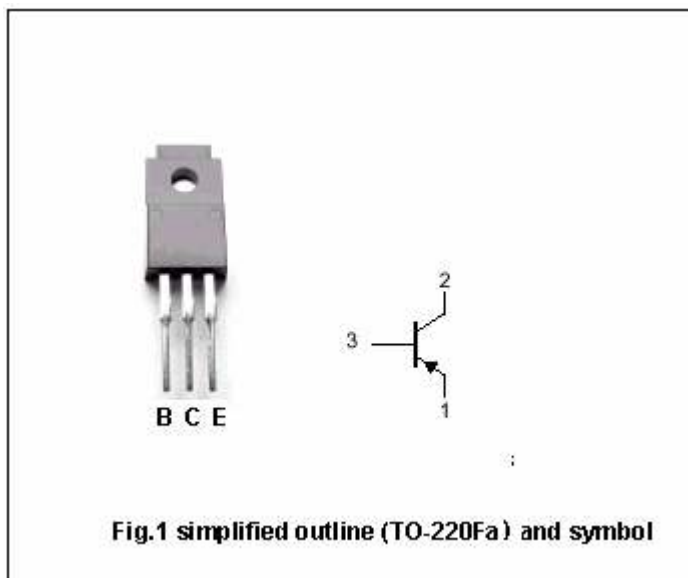
With TO-220Fa package
 Complement to type
 2SC3298,2SC3298A,2SC3298B

APPLICATIONS

Power amplifier applications
 Driver stage amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SA1306	-160	V
		2SA1306A	-180	
		2SA1306B	-200	
V _{CEO}	Collector-emitter voltage	2SA1306	-160	V
		2SA1306A	-180	
		2SA1306B	-200	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-1.5	A
I _B	Base current		-0.15	A
P _C	Collector power dissipation	T _C =25°C	20	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

Silicon PNP Power Transistors

2SA1306 2SA1306A 2SA1306B

CHARACTERISTICS

 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SA1306	-160			V
		2SA1306A	-180			
		2SA1306B	-200			
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-0.5A, I_B=-50mA$			-1.5	V
V_{BE}	Base-emitter voltage	$I_C=-0.5A, V_{CE}=-5V$			-1.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-160V, I_E=0$			-1.0	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V, I_C=0$			-1.0	μA
h_{FE}	DC current gain	$I_C=-0.1A; V_{CE}=-5V$	70		240	
C_{ob}	Output capacitance	$I_E=0; V_{CB}=-10V, f=1MHz$		30		pF
f_T	Transition frequency	$I_C=-0.1A; V_{CE}=-10V$		100		MHz

◆ h_{FE} Classifications

O	Y
70-140	120-240

PACKAGE OUTLINE

